

**AMENDMENTS TO THE CLAIMS**

1. **(Currently Amended)** ~~A compound semiconductor~~ An InP substrate for epitaxial growth,

wherein, when haze is defined as a value calculated by dividing intensity of scattered light obtained when light is incident from a predetermined light source onto a surface of ~~[[a]]~~ the InP substrate, by intensity of the incident light from the light source, the light source having a wavelength of 488 nm,

the haze is not more than ~~2 ppm~~ 1 ppm all over an effectively used area of the InP substrate and an off-angle with respect to a plane direction is 0.05 to 0.10°, wherein the effectively used area includes the surface area of the substrate, with the exception of the peripheral part including the chamfered part of the substrate.

2. **(Cancelled)**

3. **(Cancelled)**

4. **(Currently Amended)** ~~The compound semiconductor~~ InP substrate as claimed in claim 1 ~~claim 3~~, wherein a dislocation density is not more than  $1000/\text{cm}^2$ .

5. **(Currently Amended)** ~~The compound semiconductor~~ InP substrate as claimed in claim 4, wherein the dislocation density is not more than  $500/\text{cm}^2$ .

6. (New) A compound semiconductor substrate for epitaxial growth, comprising an InP substrate and at least one epitaxial layer on the InP substrate, wherein:

the InP substrate has an off-angle with respect to a plane direction of 0.05 to 0.10°,

the InP substrate has a haze of 0.5 to 0.8 ppm, and

the haze in a surface of the at least one epitaxial layer is not more than 1 ppm,

wherein haze is defined as a value calculated by dividing intensity of scattered light obtained when light is incident from a predetermined light source onto the surface of the at least one epitaxial layer or a surface of the InP substrate, by intensity of the incident light from the light source.

7. (New) An InP substrate for epitaxial growth,

wherein, when haze is defined as a value calculated by dividing intensity of scattered light obtained when light is incident from a predetermined light source onto a surface of the InP substrate, by intensity of the incident light from the light source,

the haze is not more than 1 ppm all over an effectively used area of the InP substrate, and an off-angle with respect to a plane direction is 0.05 to 0.10°.